

Abstract of the Disclosure

A high power RF amplifier utilizes dynamic biasing for transistors in an output stage of the amplifier. In one embodiment, as the magnitude of an RF signal 5 to be amplified falls below a predetermined level, the biasing signal is turned off to reduce power consumption. A gate bias voltage is used to switch the transistors off and on. A low pass filter is employed to eliminate noise generated at the output of the amplifier caused by the instantaneous switching, while not impacting the amplifier's response to low-high magnitude transients. In a further embodiment, I and Q data 10 from baseband digital data is sampled and buffered prior to being transformed and provided to a RF power amplifier. A gate bias signal is controlled based on current samples in order to control the power amplifier in a manner appropriate for the current samples when provided from the buffer.

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